

Younggul Song

List of Publications by Year in descending order

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31
papers

823
citations

516710

16
h-index

477307

29
g-index

33
all docs

33
docs citations

33
times ranked

1760
citing authors

#	ARTICLE	IF	CITATIONS
1	Resistive Switching by Percolative Conducting Filaments in Organometal Perovskite Unipolar Memory Devices Analyzed Using Current Noise Spectra. <i>Advanced Functional Materials</i> , 2022, 32, 2107727.	14.9	8
2	Highly uniform monolayer graphene synthesis <i>via</i> a facile pretreatment of copper catalyst substrates using an ammonium persulfate solution. <i>RSC Advances</i> , 2019, 9, 20871-20878.	3.6	6
3	Enhanced Charge Injection Properties of Organic Field-Effect Transistor by Molecular Implantation Doping. <i>Advanced Materials</i> , 2019, 31, e1806697.	21.0	60
4	Organic Field-Effect Transistors: Enhanced Charge Injection Properties of Organic Field-Effect Transistor by Molecular Implantation Doping (<i>Adv. Mater.</i> 10/2019). <i>Advanced Materials</i> , 2019, 31, 1970073.	21.0	2
5	High-Performance Solution-Processed Organo-Metal Halide Perovskite Unipolar Resistive Memory Devices in a Cross-Bar Array Structure. <i>Advanced Materials</i> , 2019, 31, e1804841.	21.0	100
6	Highly Reliable Superhydrophobic Protection for Organic Field-Effect Transistors by Fluoroalkylsilane-Coated TiO ₂ Nanoparticles. <i>ACS Nano</i> , 2018, 12, 11062-11069.	14.6	32
7	Investigation of Time-Dependent Resistive Switching Behaviors of Unipolar Nonvolatile Organic Memory Devices. <i>Advanced Functional Materials</i> , 2018, 28, 1801162.	14.9	34
8	Miniaturization and Integration of Organic Resistive Memory Devices. <i>Journal of the Korean Physical Society</i> , 2018, 73, 479-487.	0.7	1
9	Resistive Switching Memory: Investigation of Time-Dependent Resistive Switching Behaviors of Unipolar Nonvolatile Organic Memory Devices (<i>Adv. Funct. Mater.</i> 35/2018). <i>Advanced Functional Materials</i> , 2018, 28, 1870249.	14.9	4
10	Attachable and flexible aluminum oxide resistive non-volatile memory arrays fabricated on tape as the substrate. <i>Nanotechnology</i> , 2017, 28, 135201.	2.6	5
11	Analysis of the interface characteristics of CVD-grown monolayer MoS ₂ by noise measurements. <i>Nanotechnology</i> , 2017, 28, 145702.	2.6	14
12	Analysis of noise generation and electric conduction at grain boundaries in CVD-grown MoS ₂ field effect transistors. <i>Nanotechnology</i> , 2017, 28, 47LT01.	2.6	9
13	Electronic noise analyses on organic electronic devices. <i>Journal of Materials Chemistry C</i> , 2017, 5, 7123-7141.	5.5	16
14	Characterization of PI:PCBM organic nonvolatile resistive memory devices under thermal stress. <i>Organic Electronics</i> , 2016, 33, 48-54.	2.6	22
15	Trap-mediated electronic transport properties of gate-tunable pentacene/MoS ₂ p-n heterojunction diodes. <i>Scientific Reports</i> , 2016, 6, 36775.	3.3	54
16	Origin of multi-level switching and telegraphic noise in organic nanocomposite memory devices. <i>Scientific Reports</i> , 2016, 6, 33967.	3.3	21
17	Integration of Flexible and Microscale Organic Nonvolatile Resistive Memory Devices Using Orthogonal Photolithography. <i>Journal of Nanoscience and Nanotechnology</i> , 2016, 16, 6350-6354.	0.9	3
18	Electrical Properties of Synthesized Large-Area MoS ₂ Field-Effect Transistors Fabricated with Inkjet-Printed Contacts. <i>ACS Nano</i> , 2016, 10, 2819-2826.	14.6	64

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19	Energy Consumption Estimation of Organic Nonvolatile Memory Devices on a Flexible Plastic Substrate. <i>Advanced Electronic Materials</i> , 2015, 1, 1500186.	5.1	12
20	Interface effect in pentacene field-effect transistors from high energy proton beam irradiation. <i>Organic Electronics</i> , 2015, 27, 240-246.	2.6	7
21	1/f Noise Scaling Analysis in Unipolar-Type Organic Nanocomposite Resistive Memory. <i>ACS Nano</i> , 2015, 9, 7697-7703.	14.6	24
22	Facile anionic synthesis of a well-controlled thermally cross-linkable block copolymer for polymer-based resistive memory device applications. <i>Polymer Chemistry</i> , 2015, 6, 4264-4270.	3.9	13
23	Vertically stacked microscale organic nonvolatile memory devices toward three-dimensional high integration. <i>Organic Electronics</i> , 2015, 21, 198-202.	2.6	10
24	Enhancement of photodetection characteristics of MoS ₂ field effect transistors using surface treatment with copper phthalocyanine. <i>Nanoscale</i> , 2015, 7, 18780-18788.	5.6	101
25	4K-bit and microlithographic integration of organic nonvolatile resistive memory devices. <i>Organic Electronics</i> , 2015, 17, 192-197.	2.6	16
26	Well-Defined Block Copolymers with Triphenylamine and Isocyanate Moieties Synthesized via Living Anionic Polymerization for Polymer-Based Resistive Memory Applications: Effect of Morphological Structures on Nonvolatile Memory Performances. <i>Macromolecules</i> , 2014, 47, 8625-8633.	4.8	11
27	The application of orthogonal photolithography to micro-scale organic field effect transistors and complementary inverters on flexible substrate. <i>Applied Physics Letters</i> , 2014, 104, 053301.	3.3	20
28	Micro-scale twistable organic field effect transistors and complementary inverters fabricated by orthogonal photolithography on flexible polyimide substrate. <i>Organic Electronics</i> , 2014, 15, 2822-2829.	2.6	16
29	Irradiation Effects of High-Energy Proton Beams on MoS ₂ Field Effect Transistors. <i>ACS Nano</i> , 2014, 8, 2774-2781.	14.6	100
30	Twistable nonvolatile organic resistive memory devices. <i>Organic Electronics</i> , 2013, 14, 2087-2092.	2.6	27
31	Performance enhancement of triisopropylsilylethynyl pentacene organic field effect transistors with inkjet-printed silver source/drain electrodes achieved via dispersible reduced graphene oxide. <i>Thin Solid Films</i> , 2013, 542, 327-331.	1.8	6